HOUR EXAMINATION #2

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First Name (use capital letters):_	^		、
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2) Write your name and section at the back of the test

DO NOT TURN THIS PAGE UNTIL YOU ARE TOLD

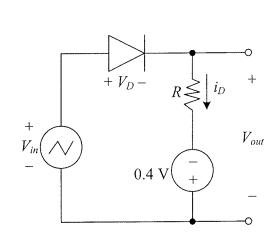
Make sure to write your name AGAIN at the top of every page of your exam.

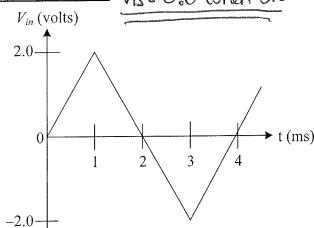
A. Write or print clearly. Answer each problem on the exam itself. If you need extra paper, there is an extra sheet at the end of this exam. Clearly identify the problem number on any additional pages. The Boolean Algebra identities are also attached to the exam.

B. In order to receive partial or full credit, you must show all your work, e.g., your solution process, the equation(s) that you use, the values of the variables used in the equation(s), etc. You must also include the unit of measurement in each answer.

Students caught cheating on this exam will earn a grade of F for the entire course. Other penalties may include suspension and/or dismissal from the university.

Problem 1 (20 points) The circuit below has a sawtooth wave voltage source with period 4 ms, a diode with $V_{on} = 0.6$ V, and a resistor $R = 9 \text{ k}\Omega$. By KVL and Ohm's Law, $V_{in} = V_D + V_{out}$, and $V_{out} = i_D R - 0.4$. To analyze this circuit, use the <u>large signal model</u>. $V_D = 0.6$ when O





- (a) [7 pts.] Express V_{out} in terms of V_{in} when the diode is <u>on</u>, and the range of V_{in} when the diode is on. Show your work.
- o Vb=Von= 0.6v ⇒ Vin=0.6 +Vou
- o check that is >0: is = (Vou +0.4)/R = Vin -0.6 +0.4 is = Vin -0.2 is >0 for Vin >0.2
- (b) [7 pts.] Express V_{out} in terms of V_{in} when the diode is off, and the range of V_{in} when the diode is off. Show your work.

 Vow = $0 \times R_{-}0.4 = 0.4$
 - o check that VD LO.6: Vb= Vin_Voui = Vin +0.4

 SoVD < 0.6 when Vin +0.4 < 0.6

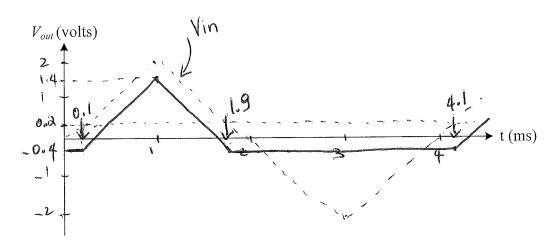
 =) when Vin < 0.2

use of these.

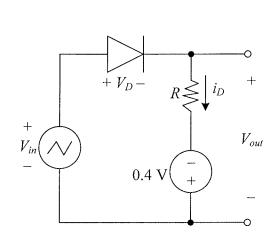
$$V_{out} = V_{in} - 0.6$$
when $0.9 < V_{in} < \infty$

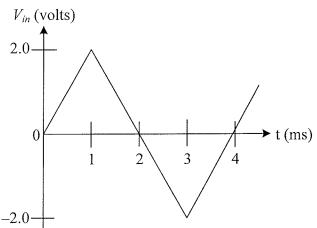
$$V_{out} = \underline{\qquad} V_{out} = \underline{\qquad} V_{in} < \underline{\qquad} V_{in} < \underline{\qquad} V_{in} < \underline{\qquad} V_{out} = \underline{\qquad} V_{out}$$

(c) [6 pts.] Plot the output voltage V_{out} for one period. Label the vertical axis with the voltages, and the horizontal axis with the times at which the behavior of the output changes.



Problem 1 (20 points) The circuit below has a sawtooth wave voltage source with period 4 ms, a diode with $V_{on} = 0.6$ V, and a resistor R = 9 k Ω . By KVL and Ohm's Law, $V_{in} = V_D + V_{out}$, and $V_{out} = i_D R - 0.4$. To analyze this circuit, use the <u>large signal model</u>.





(a) [7 pts.] Express V_{out} in terms of V_{in} when the diode is <u>on</u>, and the range of V_{in} when the diode is on. Show your work.

When the diode is or, $\bar{i}_D > 0$ and $V_D = V_{ON} = 0.6$, Thus

Void = $V_{in} - V_D = V_{in} - 0.6$.

And $i_D = \frac{V_{OUL} + 0.4}{R} = \frac{V_{in} + 0.4 - 0.6}{R}$

(b) [7 pts.] Express V_{out} in terms of V_{in} when the diode is <u>off</u>, and the range of V_{in} when the diode is off. <u>Show your work.</u>

When the diode is off, id=0 and VD < Von=0.6. So Vout = iDR-0.4 = 0-0.4 = -0.4 And VD = Vin-Vout = Vin-(iDR-0.4) = Vin +0.4 < 0.6 when Vin<0.2

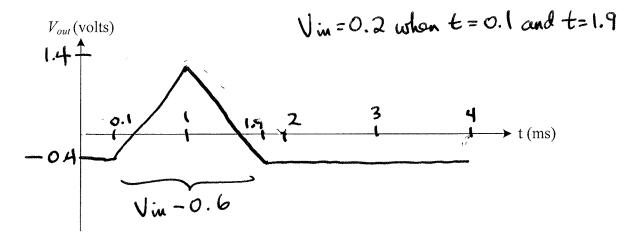
 $V_{out} = V_{in} - 0.6V$ $V_{out} = -0.4V$

when
$$O.2V$$
 $< V_{in} <$

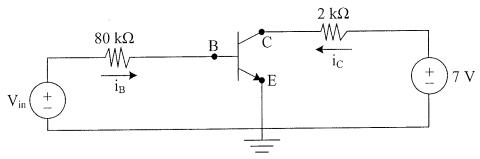
When Vin > 0.6-0.4=0.2

$$V_{out} = -0.4V$$
 when ____ < $V_{in} < 0.2V$

(c) [6 pts.] Plot the output voltage V_{out} for one period. Label the vertical axis with the voltages, and the horizontal axis with the times at which the behavior of the output changes.



Problem 2 (20 points)



$$V_{BEON} = 0.6 \text{ V}; \quad \beta = 100; \quad V_{CESAT} = 0.2 \text{ V}$$

For both parts below, use the information above to find the requested quantities and the transistor state.

(a) [10 pts.] Assume $V_{in} = 1 \text{ V. Show your work.}$

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• ON - VBE = VBEON

• Show your work.

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• Show your work.

• Show your wor

since V ce > 0 (> V ces AT) the was correct to assume active.

$$i_B = 5 \mu A$$
 $i_C = 0.5 mA$ $V_{CE} = 6V$ State Quive

(b) [10 pts.] Assume $i_C/i_B = 80$. Show your work.

» Since ic/iB = 80, this is less than B (100)

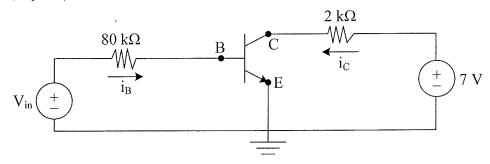
→ the transistor must be saturated.

· 80 VCE = VCESAT = O. DV ; By KVL ic = 7-0.2 = 3 .4 mA

· ic/iB=80 => iB= ic/80=3.4 mA/80=42.5 put

$$i_B = \begin{bmatrix} 42.5 \mu A \end{bmatrix}$$
 $i_C = \begin{bmatrix} 3.4 mA \end{bmatrix}$ $V_{CE} = \begin{bmatrix} 0.2 N \end{bmatrix}$ State Saturated

Problem 2 (20 points)



$$V_{BEON} = 0.6 V; \quad \beta = 100; \quad V_{CESAT} = 0.2 V$$

For both parts below, use the information above to find the requested quantities and the transistor state.

(a) [10 pts.] Assume $V_{in} = 1 \text{ V. Show your work.}$ By KVL and Ohm's Law, (2k) ic+Vc=7, Vin=(80k) iB+VBE Since Vin > VBEON, the transistor is active or saturated.

$$i_B = \frac{V_{in} - V_{BEON}}{(80k)} = \frac{1 - 0.6}{(80k)} = \frac{0.4 \text{ V}}{80k\Omega} = 5\mu\text{A}$$

If active, $i_c = (00 i_B = 100 \times 5\mu\text{A} = 0.5 \text{ mA})$
 $V_{CE} = 7 - (2k) i_c = 7 - (2k\Omega)(0.5 \text{ mA}) = 6\text{ V} < V_{CESAT}$

$$i_B = \begin{bmatrix} 5 \text{ MA} \end{bmatrix}$$
 $i_C = \begin{bmatrix} 0.5 \text{ MA} \end{bmatrix}$ $V_{CE} = \begin{bmatrix} 6 \text{ V} \end{bmatrix}$ State at $\begin{bmatrix} 2 \text{ dive} \end{bmatrix}$

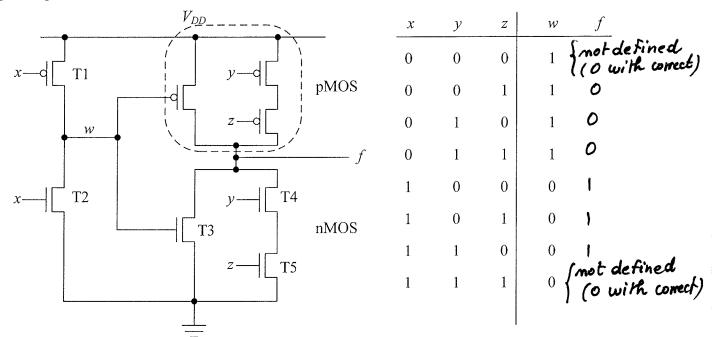
(b) [10 pts.] Assume $i_C/i_B = 80$. Show your work.

Since ic/iz=80< B, the transistor must be seturated. So VCE = VCESAT = 0.2V ic = 7-VcE = 7-0.2 = 6.8V = 3.4 mA

$$i_B = \frac{i_c}{(80k)} = \frac{3.4 \text{ mA}}{80 \text{ kg}} = 42.5 \text{ mA}$$

$$i_B = \begin{bmatrix} 42.5 \mu A \end{bmatrix}$$
 $i_C = \begin{bmatrix} 3.4 mA \end{bmatrix}$ $V_{CE} = \begin{bmatrix} 0.2 V \end{bmatrix}$ State state

Problem 3 (20 points) In the CMOS circuit below, the nMOS part is correct, but the enclosed pMOS part is incorrect.



- (a) [8 pts.] Complete the truth table for the value of f.
- **(b)** [4 pts.] Explain **in words** how the table for w was obtained.

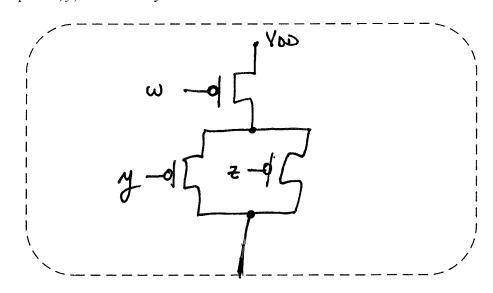
w is high (1) when x is low (0)

because Ti is on 8 Ta is off

w is low (0) when x is high (1)

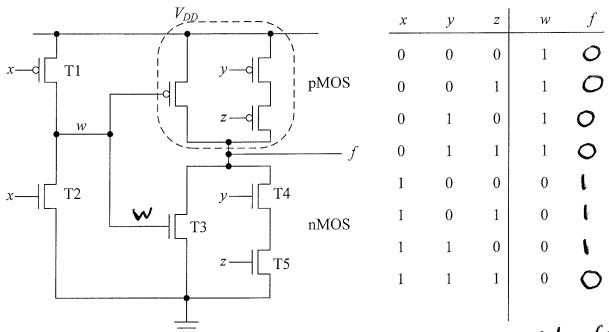
because Ti is off 8 Ta is on

(c) [8 pts.] Draw the correct pMOS portion of the circuit that corresponds to the nMOS portion. Label the inputs w, y, and z clearly.



(a) From the nMOS part, f = low (o) when W=1 or y=Z=1

Problem 3 (20 points) In the CMOS circuit below, the nMOS part is correct, but the enclosed pMOS part is incorrect.

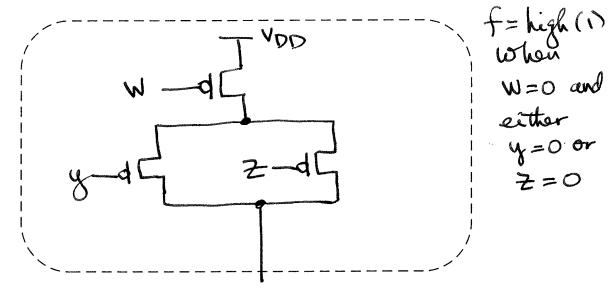


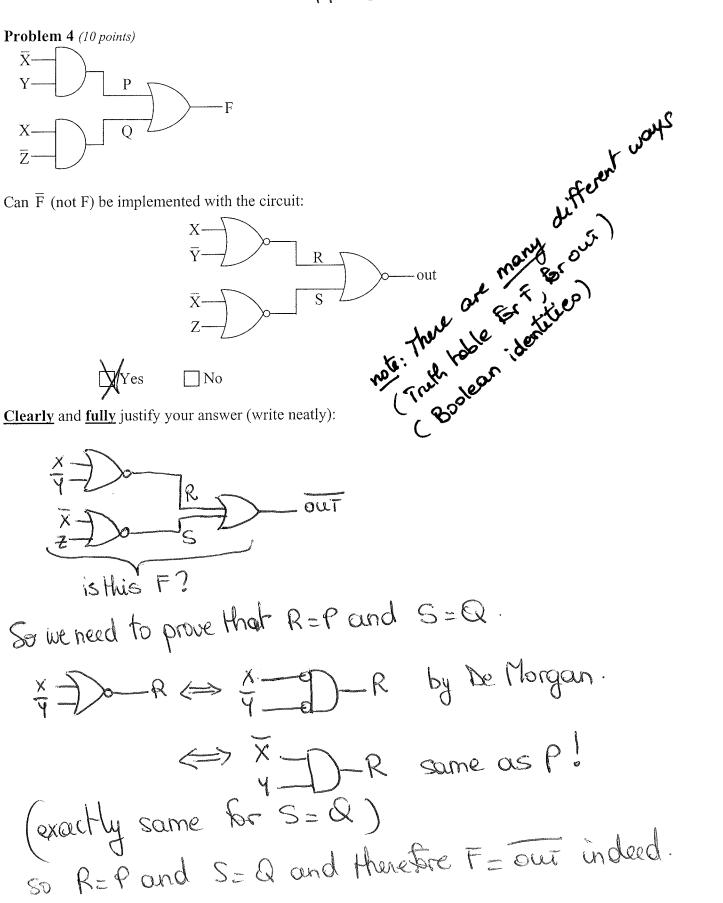
(a) [8 pts.] Complete the truth table for the value of fafter the pMOS part has been corrected (as in part (c) below)

(b) [4 pts.] Explain **in words** how the table for w was obtained.

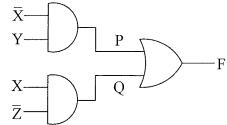
w is high (1) when χ is low (0) because T(is on and T2 is off, so wis connected to VoD = high w is low (0) when x is high (1) because T1 is off and T2 is on, so w is connected to ground (low)

(c) [8 pts.] Draw the correct pMOS portion of the circuit that corresponds to the nMOS portion. Label the inputs w, y, and z clearly.

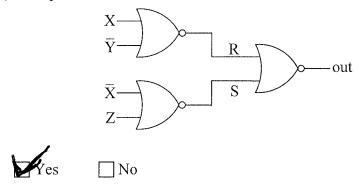




Problem 4 (10 points)



Can \overline{F} (not F) be implemented with the circuit:



<u>Clearly</u> and <u>fully</u> justify your answer (write neatly):

$$F = \overline{XY + XZ}$$

$$F = (\overline{XY + XZ}) = (\overline{XY}) \cdot (\overline{XZ}) \text{ by DeMorgan}$$

$$= (\overline{X + Y}) \cdot (\overline{X + Z}) \text{ by DeMorgan again}$$

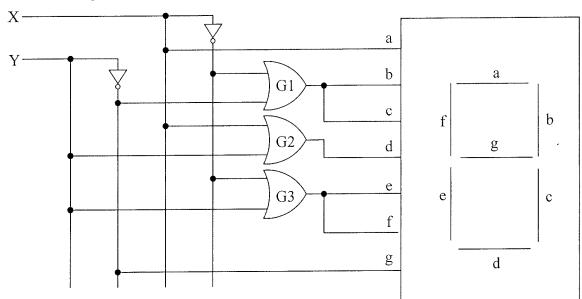
$$= (\overline{X + Y}) \cdot (\overline{X + Z}) \text{ by Involution}$$

$$Out = (\overline{X + Y}) \cdot (\overline{X + Z}) = \overline{X \cdot \overline{Y}} \cdot (\overline{X + Z})$$

$$= (\overline{X + Y}) \cdot (\overline{X + Z}) \text{ by Involution}$$

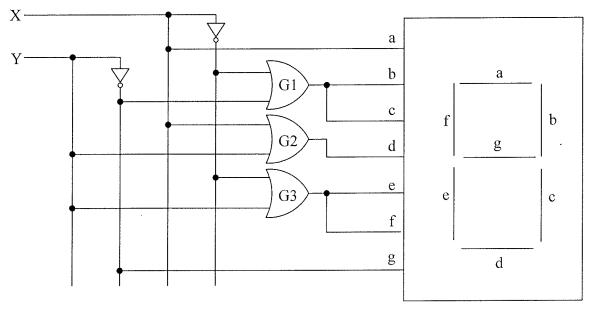
$$= \overline{F}$$

Problem 5 (15 points)



Complet	te the table	below.	Show y	our wo	rk. *****	X.	+4	4	
X	Y	a	6	c	d	e	f	g	display
0	0	0			0	· · ·		i	
0	1	0		(i.		1	0	
1	0	1	\	\	\	0	0		
1	1		O	O		A accusable		0	
	a = 1	X _ = >	7 . J			= X	9200	-+7	g = Y
	U = C	-	1+1		6		= X	+ /	

Problem 5 (15 points)



Complete the table below. Show your work.

X	Y	a	b	c	d	e	f	g	display
0	0	O	((0				1-1
0	1	0	Î	((1	0	1 1
1	0	(l	•	(0	0	(
1	1		0	0	*Supplemental Supplemental Supp			0	1_

$$a = x$$

 $b = c = \overline{x} + \overline{y}$
 $d = x + y$
 $e = f = \overline{x} + y$
 $g = \overline{y}$

Problem 6 (15 points)

For each of the following questions, check	the most	correct	answer.
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(a) It is poss of gates)		ent any Boolea	in function using only NOR gates (and no other kinds
<i>c= B</i>	•		just like NAND (we can
	True	False	just-like NAND (we can make not, AND, OR gots)
(b) It is poss of gates)		ent any Boolea	an function using only XNOR gates (and no other kinds
	True	False	A B C.
(c) (ABC) ₁₆	is an even nun	nber.	1010 1011 1100 Teven
	True	False	
(d) Adding ($(A2)_{16}$ and $(5F)_{16}$) ₁₆ leads to ove	rflow on an 8-bit parallel adder. A 2
	True	False	we would need <u>5F</u> 9 bits 101
(e) A seven-	-segment displa	ay can be used	to display any decimal digit.
	X True	☐ False	O > 9 possible (all).

Problem 6 (15 points)

For each of the following questions, check the most correct answer.

(a) It is possible to implement any Boolean function using only NOR gates (and no other kinds of gates).

 $\frac{1}{x} = \frac{1}{x} = \frac{1}$ True

(b) It is possible to implement any Boolean function using only XNOR gates (and no other kinds of gates).

True False

(c) $(ABC)_{16}$ is an even number.

(ABC)16 = (10101011 1100)2 = 2²+2³+... (no 2°) Righmost 6it is 0, so must be even True False

(d) Adding $(A2)_{16}$ and $(5F)_{16}$ leads to overflow on an 8-bit parallel adder.

10100010 True False

(e) A seven-segment display can be used to display any decimal digit.

True ☐ False